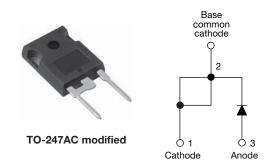
Vishay Semiconductors

HEXFRED[®] Ultrafast Soft Recovery Diode, 15 A



PRODUCT SUMMARY								
Package	TO-247AC modified (2 pins)							
I _{F(AV)}	15 A							
V _R	600 V							
V _F at I _F	1.7 V							
t _{rr} (typ.)	19 ns							
T _J max.	150 °C							
Diode variation	Single die							

FEATURES

- · Ultrafast and ultrasoft recovery
- Very low I_{BBM} and Q_{rr}
- Compliant to RoHS Directive 2002/95/EC
- Designed and gualified for industrial level

BENEFITS

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- · Reduced parts count

DESCRIPTION

VS-HFA15PB60PbF is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 15 A continuous current, the VS-HFA15PB60PbF is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{RBM}) and does not exhibit any tendency to "snap-off" during the tb portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA15PB60PbF is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Cathode to anode voltage	V _R		600	V
Maximum continuous forward current	I _F	T _C = 100 °C	15	
Single pulse forward current	I _{FSM}		150	А
Maximum repetitive forward current	I _{FRM}		60	
Maximum power dissipation	р	T _C = 25 °C	74	W
Maximum power dissipation	P _D	T _C = 100 °C	29	vv
Operating junction and storage temperature range	T _J , T _{Stg}		- 55 to + 150	°C

For technical questions within your region, please contact one of the following: DiodesAmericas@vishay.com, DiodesAsia@vishay.com, DiodesEurope@vishay.com



COMPLIANT

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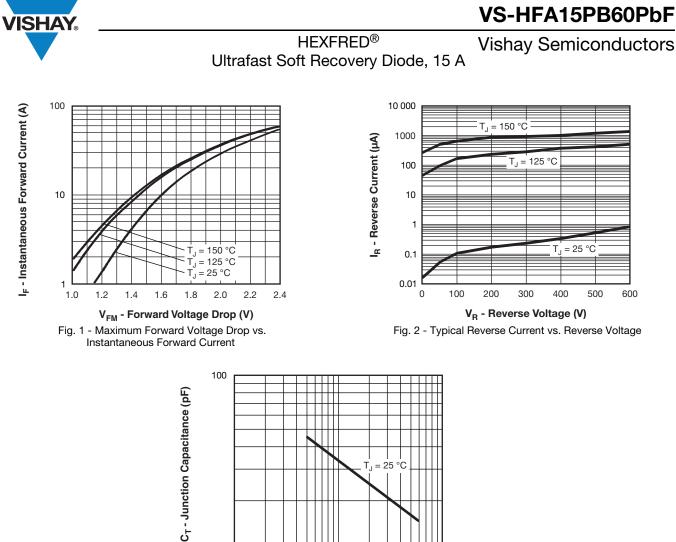
HEXFRED[®] Ultrafast Soft Recovery Diode, 15 A

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS		
Cathode to anode breakdown voltage	V _{BR}	I _R = 100 μA	600	-	-				
Maximum forward voltage	V _{FM}	I _F = 15 A		-	1.3	1.7	V		
		I _F = 30 A	See fig. 1	-	1.5	2.0			
		I _F = 15 A, T _J = 125 °C		-	1.2	1.6			
Maximum reverse		$V_R = V_R$ rated	See fig. 2	-	1.0	10	μA		
leakage current	I _{RM}	T_J = 125 °C, V_R = 0.8 x V_R rated	See lig. 2	-	400	1000			
Junction capacitance	CT	V _R = 200 V See fig. 3		-	25	50	pF		
Series inductance	L _S	Measured lead to lead 5 mm from pa	-	12	-	nH			

DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25$ °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CON	NDITIONS	MIN.	TYP.	MAX.	UNITS		
	t _{rr}	$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 200 \text{ /}$	$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 200 \text{ A}/\mu\text{s}, \text{ V}_R = 30 \text{ V}$		19	-			
Reverse recovery time See fig. 5, 10	t _{rr1}	T _J = 25 °C		-	42	60	ns		
	t _{rr2}	T _J = 125 °C		-	74	120			
Peak recovery current	I _{RRM1}	T _J = 25 °C		-	4.0	6.0	- A nC - Α/μs		
See fig. 6	I _{RRM2}	T _J = 125 °C	I _F = 15 A	-	6.5	10			
Reverse recovery charge	Q _{rr1}	T _J = 25 °C	dl _F /dt = 200 A/µs V _B = 200 V	-	80	180			
See fig. 7	Q _{rr2}	T _J = 125 °C	V _R = 200 V	-	220	600			
Peak rate of fall of recovery current during t _b	dl _{(rec)M} /dt1	T _J = 25 °C		-	188	-			
See fig. 8	dl _{(rec)M} /dt2	T _J = 125 °C		-	160	-			

THERMAL - MECHANICAL SPECIFICATIONS										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C				
Thermal resistance, junction to case	R _{thJC}		-	-	1.7					
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	40	K/W				
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.25						
Weight			-	6.0	-	g				
weight			-	0.21	-	oz.				
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)				
Marking device		Case style TO-247AC modified (JEDEC)	HFA15PB60							

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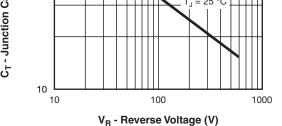


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

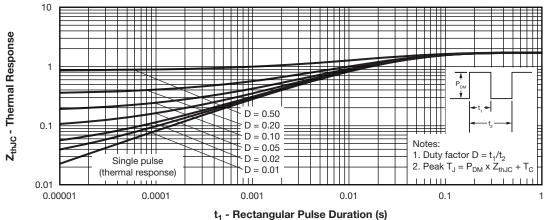


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

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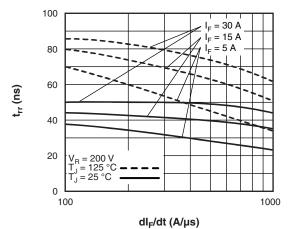


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt

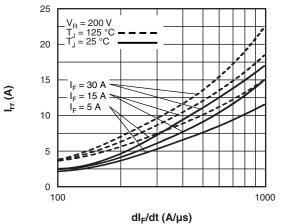
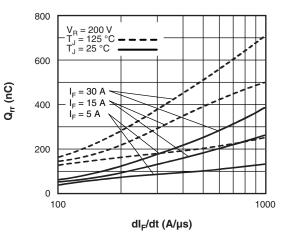
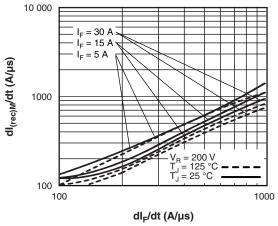


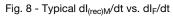
Fig. 6 - Typical Recovery Current vs. dl_F/dt



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Fig. 7 - Typical Stored Charge vs. dl_F/dt





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HEXFRED[®] Ultrafast Soft Recovery Diode, 15 A

Vishay Semiconductors

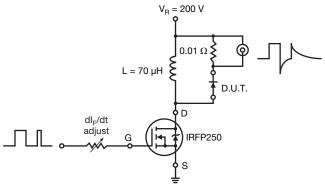
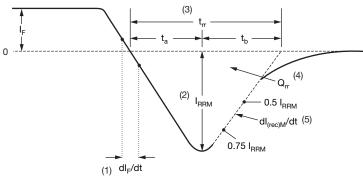


Fig. 9 - Reverse Recovery Parameter Test Circuit



(1) dI_F/dt - rate of change of current through zero crossing

(4) ${\rm Q}_{\rm rr}$ - area under curve defined by ${\rm t}_{\rm rr}$ and ${\rm I}_{\rm RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(2) I_{RRM} - peak reverse recovery current

(3) t_{rr} - reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.

(5) $dl_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

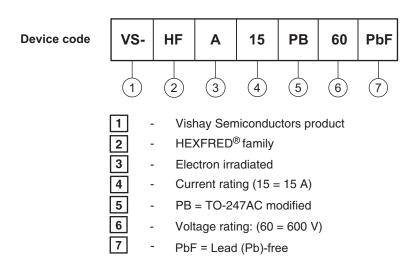
Fig. 10 - Reverse Recovery Waveform and Definitions

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HEXFRED[®] Ultrafast Soft Recovery Diode, 15 A



ORDERING INFORMATION TABLE



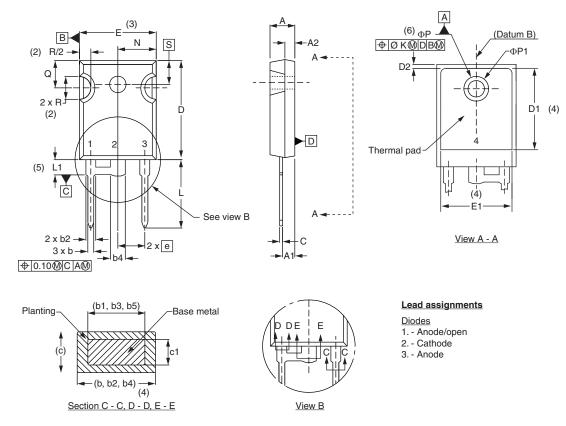
LINKS TO RELATED DOCUMENTS						
Dimensions www.vishay.com/doc?95253						
Part marking information	www.vishay.com/doc?95255					

Outline Dimensions





DIMENSIONS in millimeters and inches



SYMBOL	MILLIM	IETERS	INC	HES	NOTES	SYMBOL	MILLIMETERS		INCHES		NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	STINDOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.65	5.31	0.183	0.209		D2	0.51	1.30	0.020	0.051	
A1	2.21	2.59	0.087	0.102		E	15.29	15.87	0.602	0.625	3
A2	1.50	2.49	0.059	0.098		E1	13.72	-	0.540	-	
b	0.99	1.40	0.039	0.055		е	5.46	BSC	0.215	BSC	
b1	0.99	1.35	0.039	0.053		ΦK	2.	54	0.0)10	
b2	1.65	2.39	0.065	0.094		L	14.20	16.10	0.559	0.634	
b3	1.65	2.37	0.065	0.094		L1	3.71	4.29	0.146	0.169	
b4	2.59	3.43	0.102	0.135		N	7.62 BSC		0.3		
b5	2.59	3.38	0.102	0.133		ΦР	3.56	3.66	0.14	0.144	
С	0.38	0.86	0.015	0.034		Φ P1	-	6.98	-	0.275	
c1	0.38	0.76	0.015	0.030		Q	5.31	5.69	0.209	0.224	
D	19.71	20.70	0.776	0.815	3	R	4.52	5.49	1.78	0.216	
D1	13.08	-	0.515	-	4	S	5.51	BSC	0.217	BSC	

Notes

⁽¹⁾ Dimensioning and tolerance per ASME Y14.5M-1994

(2) Contour of slot optional

(3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

- ⁽⁴⁾ Thermal pad contour optional with dimensions D1 and E1
- ⁽⁵⁾ Lead finish uncontrolled in L1

(6) ΦP to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")

⁽⁷⁾ Outline conforms to JEDEC outline TO-247 with exception of dimension c

Revision: 21-Jun-11

1

Document Number: 95253

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